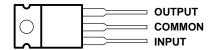
- 3-Terminal Regulators
- Output Current Up to 1.5 A
- Internal Thermal Overload Protection
- High Power Dissipation Capability
- Internal Short-Circuit Current Limiting
- Output Transistor Safe-Area Compensation
- Direct Replacements for Fairchild μA7800 Series

description

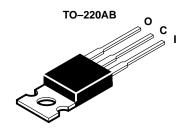
This series of fixed-voltage monolithic integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 1.5 A of output current. The internal current limiting and thermal shutdown features of these regulators make them essentially immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents and also used as the power-pass element in precision regulators.

The μ A7800C series is characterized for operation over the virtual junction temperature range of 0°C to 125°C. The μ A7805Q and μ A7812Q are characterized for operation over the virtual junction temperature range of -40°C to 125°C.

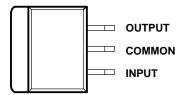
KC PACKAGE (TOP VIEW)



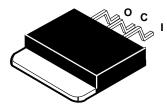
The common terminal is in electrical contact with the mounting base.



KTE PACKAGE (TOP VIEW)



The common terminal is in electrical contact with the mounting base.



AVAILABLE OPTIONS

		PACKAGED	DEVICES	
ТЈ	V _{O(nom)} (V)	PLASTIC FLANGE-MOUNT (KC)	HEAT-SINK MOUNTED _† (KTE)	CHIP FORM (Y)
	5	μΑ7805CKC	μΑ7805CKTE	μΑ7805Υ
	6	μΑ7806CKC	μΑ7806CKTE	μΑ7806Υ
	8	μΑ7808CKC	μΑ7808CKTE	μΑ7808Υ
	8.5	μΑ7885CKC	μΑ7885CKTE	μΑ7885Υ
0°C to 125°C	10	μΑ7810CKC	μΑ7810CKTE	μΑ7810Y
	12	μΑ7812CKC	μΑ7812CKTE	μΑ7812Y
	15	μΑ7815CKC	μΑ7815CKTE	μΑ7815Y
	18	μΑ7818CKC	μΑ7818CKTE	μΑ7818Y
	24	μΑ7824CKC	μΑ7824CKTE	μΑ7824Y
-40°C to 125°C	5	μΑ7805QKC	μΑ7805QKTE	_
-40 C to 125 C	12	μΑ7812QKC	μΑ7812QKTE	_

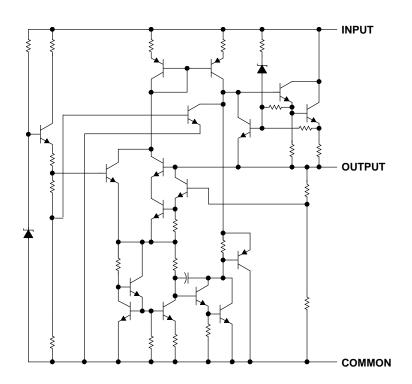
[†] The KTE package is also available taped and reeled.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

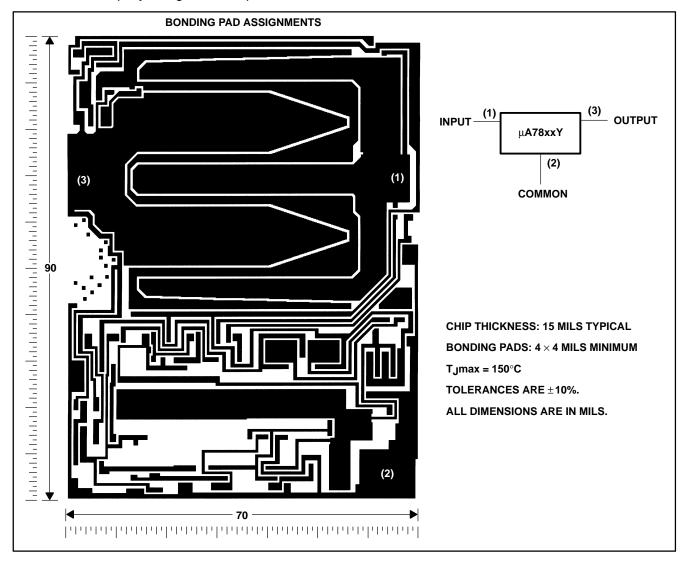


schematic



μΑ78xxY chip information

These chips, when properly assembled, display characteristics similar to the μ A78xxC. Thermal compression or ultrasonic bonding may be used on the doped aluminum bonding pads. The chips may be mounted with conductive epoxy or a gold-silicon preform.



absolute maximum ratings over operating temperature ranges (unless otherwise noted)†

NOTE 1: For operation above 25°C free-air or 90°C case temperature, refer to Figure 1 and Figure 2. To avoid exceeding the design maximum virtual junction temperature, these ratings should not be exceeded. Due to variations in individual device electrical characteristics and thermal resistance, the built-in thermal overload protection may be activated at power levels slightly above or below the rated dissipation.

DISSIPATION RATING TABLE — FREE-AIR TEMPERATURE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 105°C POWER RATING	T _A = 125°C POWER RATING
KC	2000 mW	16.0 mW/°C	1280 mW	720 mW	400 mW
KTE	1900 mW	15.2 mW/°C	1216 mW	684 mW	380 mW

DISSIPATION RATING TABLE — CASE TEMPERATURE

PACKAGE	T _C ≤ 90°C POWER RATING	DERATING FACTOR ABOVE T _C = 90°C	T _A = 125°C POWER RATING
KC	15000 mW	250.0 mW/°C	6250 mW
KTE	14300 mW	238.0 mW/°C	5970 mW

FREE-AIR TEMPERATURE DISSIPATATION DERATING CURVE

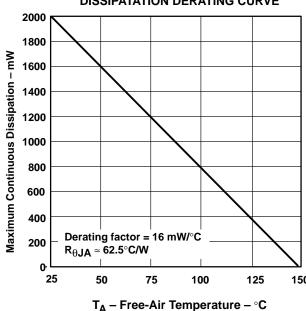


Figure 1

CASE TEMPERATURE

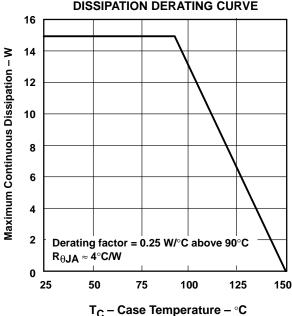


Figure 2



[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		MIN	MAX	UNIT
	μΑ7805C	7	25	
	μΑ7806C	8	25	
	μΑ7808C	10.5	25	
	μΑ7885C	10.5	25	
Input voltage, V _I	μΑ7810C	12.5	28	V
	μΑ7812C	14.5	30	
	μΑ7815C	17.5	30	
	μΑ7818C	21	33	
	μΑ7824C	27	38	
Output current, IO			1.5	Α
Operating virtual junction temperature, Tu	μΑ7800C Series	0	125	°C
out current, I _O	μΑ7805Q, μΑ7812Q	-40	125)

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST COMPITIONS	- +	μ Α780	5C, μ Α 7	805Q	LINUT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIT
		25°C	4.8	5	5.2	
Output voltage [‡]	$I_O = 5$ mA to 1 A, $V_I = 7$ V to 20 V, $P \le 15$ W	Full range§	4.75		5.25	V
land traite and an endation	V _I = 7 V to 25 V	0500		3	100	\/
Input voltage regulation	V _I = 8 V to 12 V	25°C		1	50	m∨
Ripple rejection	V _I = 8 V to 18 V, f = 120 Hz	Full range§	62	78		dB
Output voltage regulation	I _O = 5 mA to 1.5 A	0500		15	100	mV
	I _O = 250 mA to 750 mA	25°C		5	50	mv
Output resistance	f = 1 kHz	Full range§		0.017		Ω
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	Full range§		-1.1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		40		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.2	8	mA
Dies summent change	V _I = 7 V to 25 V	F. II 8			1.3	A
Bias current change	I _O = 5 mA to 1 A	Full range§			0.5	mA
Short-circuit output current		25°C		750		mA
Peak output current		25°C		2.2		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for the μA7805C and –40°C to 125°C for the μA7805Q.

electrical characteristics at specified virtual junction temperature, V_I = 11 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	- t	μ	A7806C		LINIT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIT
		25°C	5.75	6	6.25	
Output voltage [‡]	I_O = 5 mA to 1 A, V_I = 8 V to 21 V, $P \le$ 15 W	0°C to 125°C	5.7		6.3	V
Input valtage regulation	V _I = 8 V to 25 V	25°C		5	120	mV
Input voltage regulation	V _I = 9 V to 13 V	25.0		1.5	60	IIIV
Ripple rejection	V _I = 9 V to 19 V, f = 120 Hz	0°C to 125°C	59	75		dB
Output voltage regulation	I _O = 5 mA to 1.5 A	0500		14	120	\/
	I _O = 250 mA to 750 mA	25°C		4	60	mV
Output resistance	f = 1 kHz	0°C to 125°C		0.019		Ω
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.8		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		45		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.3	8	mA
Diag assument about as	V _I = 8 V to 25 V	000 +- 40500			1.3	A
Bias current change	I _O = 5 mA to 1 A	0°C to 125°C	0.5			mA
Short-circuit output current		25°C		550		mA
Peak output current		25°C		2.2		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 500 mA (unless otherwise noted)

PARAMETER	TEST CONDITIONS	t	μ Α7808C			UNIT
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	UNIT
		25°C	7.7	8	8.3	
Output voltage‡	I_O = 5 mA to 1 A, V_I = 10.5 V to 23 V, $P \le$ 15 W	0°C to 125°C	7.6		8.4	V
Input valtage regulation	V _I = 10.5 V to 25 V	25°C		6	160	mV
Input voltage regulation	V _I = 11 V to 17 V	25 0		2	80	IIIV
Ripple rejection	V _I = 11.5 V to 21.5 V, f = 120 Hz	0°C to 125°C	55	72		dB
Output voltage regulation $ \frac{I_{O} = 5 \text{ mA to } 1.5 \text{ A}}{I_{O} = 250 \text{ mA to } 750 \text{ A}} $ 25°C	I _O = 5 mA to 1.5 A	0500	35°C	12	160	mV
		4	80	mv		
Output resistance	f = 1 kHz	0°C to 125°C		0.016		Ω
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	0°C to 125°C		-0.8		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		52		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.3	8	mA
Dies surrent shangs	V _I = 10.5 V to 25 V	0°C to 125°C			1	mA
Bias current change	I _O = 5 mA to 1 A	0.0 10 125.0	25 0		0.5	mA
Short-circuit output current		25°C		450		mA
Peak output current		25°C		2.2		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, V_I = 15 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST COMPITIONS	+ +	μ Α7885C			UNIT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNII
		25°C	8.15	8.5	8.85	
Output voltage [‡]	I_O = 5 mA to 1 A, V_I = 11 V to 23.5 V, $P \le$ 15 W	0°C to 125°C	8.1		8.9	V
Input valtage regulation	V _I = 10.5 V to 25 V	25°C		6	170	mV
Input voltage regulation	V _I = 11 V to 17 V	25-0		2	85	IIIV
Ripple rejection	V _I = 11.5 V to 21.5 V, f = 120 Hz	0°C to 125°C	54	70		dB
Outrod wells as as soleties	I _O = 5 mA to 1.5 A	0500		12	170	\/
Output voltage regulation	I _O = 250 mA to 750 mA	25°C		4	85	mV
Output resistance	f = 1 kHz	0°C to 125°C		0.016		Ω
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-0.8		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		55		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.3	8	mA
Diag surrent shares	V _I = 10.5 V to 25 V	000 +- 40500			1	Λ
Bias current change	I _O = 5 mA to 1 A	0°C to 125°C			0.5	mA
Short-circuit output current		25°C		450		mA
Peak output current		25°C		2.2		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 17 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	- .+	μ Α7810C			UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	UNII	
		25°C	9.6	10	10.4		
Output voltage [‡]	I_O = 5 mA to 1 A, V_I = 12.5 V to 25 V, $P \le 15$ W	0°C to 125°C	9.5	10	10.5	V	
lanut voltage regulation	V _I = 12.5 V to 28 V	2500		7	200	\/	
Input voltage regulation	V _I = 14 V to 20 V	25°C		2	100	m∨	
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	0°C to 125°C	55	71		dB	
Outrot valle as as addition	I _O = 5 mA to 1.5 A	0500	25°C		12	200	\/
Output voltage regulation	I _O = 250 mA to 750 mA	25-0		4	100	m∨	
Output resistance	f = 1 kHz	0°C to 125°C		0.018		Ω	
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	0°C to 125°C		-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		70		μV	
Dropout voltage	I _O = 1 A	25°C		2		V	
Bias current		25°C		4.3	8	mA	
Disc surrent shares	V _I = 12.5 V to 28 V	000 +- 40500			1	A	
Bias current change	I _O = 5 mA to 1 A	0°C to 125°C			0.5	mA	
Short-circuit output current		25°C		400		mA	
Peak output current		25°C		2.2		Α	

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST COMPLTIONS	- t	μ Α7812C			LINIT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIT
		25°C	11.5	12	12.5	
Output voltage [‡]	I_{O} = 5 mA to 1 A, V_{I} = 14.5 V to 27 V, $P \le$ 15 W	Full range§	11.4		12.6	V
lanut voltage regulation	V _I = 14.5 V to 30 V	25°C		10	240	mV
Input voltage regulation	V _I = 16 V to 22 V	25 C		3	120	IIIV
Ripple rejection	V _I = 15 V to 25 V, f = 120 Hz	Full range§	55	71		dB
Outrot valta na namulation	I _O = 5 mA to 1.5 A	0500		12	240	>/
Output voltage regulation	I _O = 250 mA to 750 mA	25°C	4 1		120	m∨
Output resistance	f = 1 kHz	Full range§		0.018		Ω
Temperature coefficient of output voltage	I _O = 5 mA	Full range§		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		75		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.3	8	mA
Dies surrent shangs	V _I = 14.5 V to 30 V	Full remark	-		1	A
Bias current change	I _O = 5 mA to 1 A	Full range§			0.5	mA
Short-circuit output current		25°C		350		mA
Peak output current		25°C		2.2		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 23 \text{ V}$, $I_O = 500 \text{ mA}$ (unless otherwise noted)

DADAMETED	TEST COMPITIONS	T.+	μ	A7815C	;	UNIT	
PARAMETER	TEST CONDITIONS	TJ [†]	MIN	TYP	MAX	UNII	
		25°C	14.4	15	15.6		
Output voltage [‡]	I_O = 5 mA to 1 A, V_I = 17.5 V to 30 V $P \le$ 15 W	0°C to 125°C	14.25		15.75	V	
land the same and the same	V _I = 17.5 V to 30 V	0500		11	300	\/	
Input voltage regulation	V _I = 20 V to 26 V	25°C		3	150	mV	
Ripple rejection	V _I = 18.5 V to 28.5 V, f = 120 Hz	0°C to 125°C	54	70		dB	
Output and to me an analytical	I _O = 5 mA to 1.5 A	0500		12	300	\/	
Output voltage regulation	I _O = 250 mA to 750 mA	25°C		4	150	mV	
Output resistance	f = 1 kHz	0°C to 125°C		0.019		Ω	
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-1		mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz	25°C		90		μV	
Dropout voltage	I _O = 1 A	25°C		2		V	
Bias current		25°C		4.4	8	mA	
Dies sument ab care	V _I = 17.5 V to 30 V	000 +- 40500			1	A	
Bias current change	I _O = 5 mA to 1 A	0°C to 125°C	0°C to 125°C		0.5	mA	
Short-circuit output current		25°C		230		mA	
Peak output current		25°C		2.1		Α	

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[§] Full range virtual junction temperature is 0°C to 125°C for the μA7812C and –40°C to 125°C for the μA7812Q.

electrical characteristics at specified virtual junction temperature, V_I = 27 V, I_O = 500 mA (unless otherwise noted)

DADAMETED	TEST CONDITIONS	- t	μ Α7818C			LINUT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIT
		25°C	17.3	18	18.7	
Output voltage‡	I_O = 5 mA to 1 A, V_I = 21 V to 33 V, $P \le$ 15 W	0°C to 125°C	17.1		18.9	V
lanut voltage regulation	V _I = 21 V to 33 V	25°C		15	360	mV
Input voltage regulation	V _I = 24 V to 30 V	25.0		5	180	IIIV
Ripple rejection	V _I = 22 V to 32 V, f = 120 Hz	0°C to 125°C	53	69		dB
Output voltage regulation	I _O = 5 mA to 1.5 A	0500		12	360	\/
	I _O = 250 mA to 750 mA	25°C	25°C 4		180	180 mV
Output resistance	f = 1 kHz	0°C to 125°C		0.022		Ω
Temperature coefficient of output voltage	I _O = 5 mA	0°C to 125°C		-1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		110		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.5	8	mA
Diag surrent shares	V _I = 21 V to 33 V	00C to 4050C			1	A
Bias current change	I _O = 5 mA to 1 A	0°C to 125°C			0.5	mA
Short-circuit output current		25°C		200		mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.

electrical characteristics at specified virtual junction temperature, V_I = 33 V, I_O = 500 mA (unless otherwise noted)

DADAMETER	TEST CONDITIONS	T.1	μ Α7824C			UNIT
PARAMETER	TEST CONDITIONS	T _J †	MIN	TYP	MAX	UNIT
		25°C	23	24	25	
Output voltage [‡]	I_O = 5 mA to 1 A, V_I = 27 V to 38 V, $P \le$ 15 W	0°C to 125°C	22.8		25.2	V
lanut voltage regulation	V _I = 27 V to 38 V	2500		18	480	\/
Input voltage regulation	V _I = 30 V to 36 V	25°C		6	240	mV
Ripple rejection	V _I = 28 V to 38 V, f = 120 Hz	0°C to 125°C	50	66		dB
Output voltage regulation	I _O = 5 mA to 1.5 A	0500		12	480	>/
	I _O = 250 mA to 750 mA	25°C		4 240		m∨
Output resistance	f = 1 kHz	0°C to 125°C		0.028		Ω
Temperature coefficient of output voltage	$I_O = 5 \text{ mA}$	0°C to 125°C		-1.5		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	25°C		170		μV
Dropout voltage	I _O = 1 A	25°C		2		V
Bias current		25°C		4.6	8	mA
Bias current change	V _I = 27 V to 38 V	0°C to 125°C		1	A	
	I _O = 5 mA to 1 A			0.5	mA 5	
Short-circuit output current		25°C		150		mA
Peak output current		25°C		2.1		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 10 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7805Υ	UNIT	
PARAMETER	TEST CONDITIONS	MIN TYP MAX	ן יואט ן	
Output voltage [‡]		5	V	
Input voltage regulation	V _I = 7 V to 25 V	3	m)/	
	V _I = 8 V to 12 V	1	mV	
Ripple rejection	$V_I = 8 \text{ V to } 18 \text{ V}, \qquad f = 120 \text{ Hz}$	78	dB	
Output voltage regulation	I _O = 5 mA to 1.5 A	15	mV	
	I _O = 250 mA to 750 mA	5		
Output resistance	f = 1 kHz	0.017	Ω	
Temperature coefficient of output voltage	I _O = 5 mA	-1.1	mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz	40	μV	
Dropout voltage	I _O = 1 A	2	V	
Bias current		4.2	mA	
Short-circuit output current		750	mA	
Peak output current		2.2	Α	

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 11 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7806Υ	UNIT	
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNII	
Output voltage [‡]		6	V	
Input voltage regulation	V _I = 8 V to 25 V	5	>/	
	V _I = 9 V to 13 V	1.5	mV	
Ripple rejection	$V_1 = 9 \text{ V to } 19 \text{ V}, \qquad f = 120 \text{ Hz}$	75	dB	
Output voltage regulation	I _O = 5 mA to 1.5 A	14	mV	
	I _O = 250 mA to 750 mA	4		
Output resistance	f = 1 kHz	0.019	Ω	
Temperature coefficient of output voltage	I _O = 5 mA	-0.8	mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz	45	μV	
Dropout voltage	I _O = 1 A	2	V	
Bias current		4.3	mA	
Short-circuit output current		550	mA	
Peak output current		2.2	Α	

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 14 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7808Υ	UNIT
PARAMETER	TEST CONDITIONS	MIN TYP MAX	
Output voltage [‡]		8	V
Input voltage regulation	V _I = 10.5 V to 25 V	6	mV
	$V_{I} = 11 \text{ V to } 17 \text{ V}$	2] IIIV
Ripple rejection	$V_1 = 11.5 \text{ V to } 21.5 \text{ V}, f = 120 \text{ Hz}$	72	dB
Output voltage regulation	I _O = 5 mA to 1.5 A	12	\/
	I _O = 250 mA to 750 A	4	d m∨
Output resistance	f = 1 kHz	0.016	Ω
Temperature coefficient of output voltage	I _O = 5 mA	-0.8	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	52	μV
Dropout voltage	I _O = 1 A	2	V
Bias current		4.3	mA
Short-circuit output current		450	mA
Peak output current		2.2	Α

T Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 15 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST COMPITIONS	μ Α7885Υ	
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
Output voltage [‡]		8.5	V
lanut valtage regulation	V _I = 10.5 V to 25 V	6	\/
nput voltage regulation	V _I = 11 V to 17 V	2	mV
Ripple rejection	V _I = 11.5 V to 21.5 V, f = 120 Hz	70	dB
Output voltage regulation	I _O = 5 mA to 1.5 A	12	\/
	I _O = 250 mA to 750 mA	4	mV
Output resistance	f = 1 kHz	0.016	Ω
Temperature coefficient of output voltage	I _O = 5 mA	-0.8	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	55	μV
Dropout voltage	I _O = 1 A	2	V
Bias current		4.3	mA
Short-circuit output current		450	mA
Peak output current		2.2	Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



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[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 17 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7810Υ	UNIT	
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNII	
Output voltage [‡]		10	V	
Input voltage regulation	V _I = 12.5 V to 28 V	7		
	V _I = 14 V to 20 V	2	mV	
Ripple rejection	V _I = 13 V to 23 V, f = 120 Hz	71	dB	
Output voltage regulation	I _O = 5 mA to 1.5 A	12	mV	
	I _O = 250 mA to 750 mA	4		
Output resistance	f = 1 kHz	0.018	Ω	
Temperature coefficient of output voltage	I _O = 5 mA	-1	mV/°C	
Output noise voltage	f = 10 Hz to 100 kHz	70	μV	
Dropout voltage	I _O = 1 A	2	V	
Bias current		4.3	mA	
Short-circuit output current		400	mA	
Peak output current		2.2	Α	

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 19 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7812Y	UNIT
PARAMETER	TEST CONDITIONS	MIN TYP MAX	וואט
Output voltage [‡]		12	V
Input voltage regulation	V _I = 14.5 V to 30 V	10	\/
	V _I = 16 V to 22 V	3	mV
Ripple rejection	$V_I = 15 \text{ V to } 25 \text{ V}, \qquad f = 120 \text{ Hz}$	71	dB
Output voltage regulation	I _O = 5 mA to 1.5 A	12	\/
	I _O = 250 mA to 750 mA	4	mV
Output resistance	f = 1 kHz	0.018	Ω
Temperature coefficient of output voltage	I _O = 5 mA	-1	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	75	μV
Dropout voltage	I _O = 1 A	2	V
Bias current		4.3	mA
Short-circuit output current		350	mA
Peak output current		2.2	Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



[‡]This specification applies only for dc power dissipation permitted by absolute maximum ratings.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

electrical characteristics at specified virtual junction temperature, $V_I = 23 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7815 Υ	UNIT
PARAMETER	TEST CONDITIONS	MIN TYP MAX	
Output voltage [‡]		15	V
Input voltage regulation	V _I = 17.5 V to 30 V	11	mV
	$V_{I} = 20 \text{ V to } 26 \text{ V}$	3] IIIV
Ripple rejection	$V_I = 18.5 \text{ V to } 28.5 \text{ V}, f = 120 \text{ Hz}$	70	dB
Output voltage regulation	I _O = 5 mA to 1.5 A	12	\/
	I _O = 250 mA to 750 mA	4	d m∨
Output resistance	f = 1 kHz	0.019	Ω
Temperature coefficient of output voltage	I _O = 5 mA	-1	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	90	μV
Dropout voltage	I _O = 1 A	2	V
Bias current		4.4	mA
Short-circuit output current		230	mA
Peak output current		2.1	Α

T Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

electrical characteristics at specified virtual junction temperature, $V_I = 27 \text{ V}$, $I_O = 500 \text{ mA}$, $T_J = 25^{\circ}\text{C}^{\dagger}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	μ Α7818 Υ	
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
Output voltage [‡]		18	V
Input voltage regulation	V _I = 21 V to 33 V	15	mV
	V _I = 24 V to 30 V	5] ""
Ripple rejection	V _I = 22 V to 32 V, f = 120 Hz	69	dB
Output voltage regulation	I _O = 5 mA to 1.5 A	12	\/
	I _O = 250 mA to 750 mA	4	m∨
Output resistance	f = 1 kHz	0.022	Ω
Temperature coefficient of output voltage	I _O = 5 mA	-1	mV/°C
Output noise voltage	f = 10 Hz to 100 kHz	110	μV
Dropout voltage	I _O = 1 A	2	V
Bias current		4.5	mA
Short-circuit output current		200	mA
Peak output current		2.1	Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.

[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

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μA7800 SERIES POSITIVE-VOLTAGE REGULATORS

SLVS056B - MAY 1976 - REVISED OCTOBER 1996

electrical characteristics at specified virtual junction temperature, V_I = 33 V, I_O = 500 mA, T_J = 25°C[†] (unless otherwise noted)

DADAMETER	TEST COMPITIONS	μ Α	μ Α7824Υ		
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Output voltage [‡]			24		V
Input voltage regulation	V _I = 27 V to 38 V		18		.,
	V _I = 30 V to 36 V		6		mV
Ripple rejection	$V_I = 28 \text{ V to } 38 \text{ V}, \qquad f = 120 \text{ Hz}$		66		dB
Output voltage regulation	I _O = 5 mA to 1.5 A		12		
	I _O = 250 mA to 750 mA		4		m∨
Output resistance	f = 1 kHz		0.028		Ω
Temperature coefficient of output voltage	I _O = 5 mA		-1.5		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz		170		μV
Dropout voltage	I _O = 1 A		2		V
Bias current			4.6		mA
Short-circuit output current			150		mA
Peak output current			2.1		Α

[†] Pulse-testing techniques maintain the junction temperature as close to the ambient temperature as possible. Thermal effects must be taken into account separately. All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output.



[‡] This specification applies only for dc power dissipation permitted by absolute maximum ratings.

APPLICATION INFORMATION

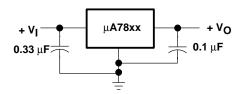


Figure 3. Fixed Output Regulator

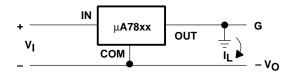
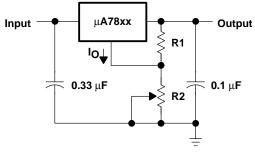


Figure 4. Positive Regulator in Negative Configuration (V_I Must Float)



NOTE A: The following formula is used when Vxx is the nominal output voltage (output to common) of the fixed regulator.

$$V_{O} = V_{XX} + \left(\frac{V_{XX}}{R1} + I_{Q}\right) R2$$

Input $\mu A78xx$ $0.33 \mu F$ $V_{O(Reg)}$ $V_$

Figure 5. Adjustable Output Regulator

Figure 6. Current Regulator

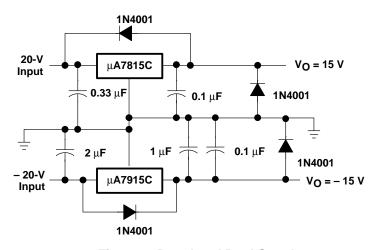


Figure 7. Regulated Dual Supply

APPLICATION INFORMATION

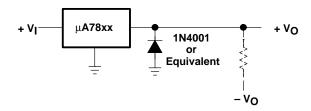


Figure 8. Output Polarity-Reversal Protection Circuit

operation with a load common to a voltage of opposite polarity

In many cases, a regulator powers a load that is not connected to ground but instead is connected to a voltage source of opposite polarity (e.g., op amps, level-shifting circuits, etc.). In these cases, a clamp diode should be connected to the regulator output as shown in Figure 8. This protects the regulator from output polarity reversals during startup and short-circuit operation.

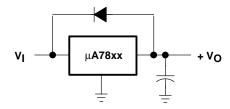


Figure 9. Reverse-Bias Protection Circuit

reverse-bias protection

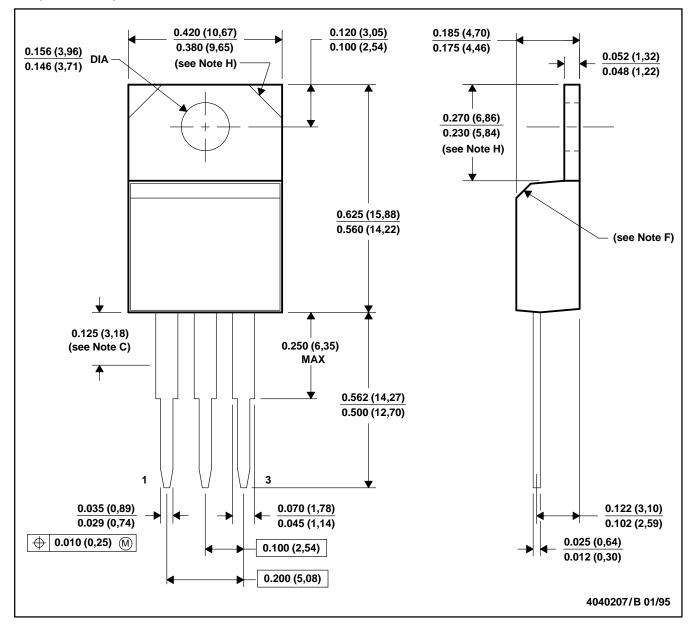
Occasionally, there exists the possibility that the input voltage to the regulator can collapse faster than the output voltage. This could occur, for example, when the input supply is crowbarred during an output overvoltage condition. If the output voltage is greater than approximately 7 V, the emitter-base junction of the series pass element (internal or external) could break down and be damaged. To prevent this, a diode shunt can be employed as shown in Figure 9.



MECHANICAL INFORMATION

KC (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: B. All linear dimensions are in inches (millimeters).

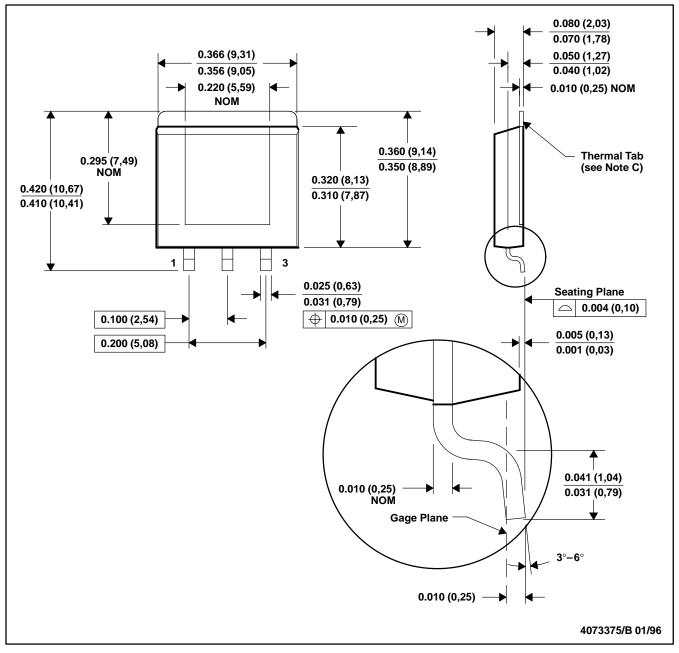
- C. This drawing is subject to change without notice.
- D. Lead dimensions are not controlled within this area.
- E. All lead dimensions apply before solder dip.
- F. The center lead is in electrical contact with the mounting tab.
- G. The chamfer is optional.
- H. Falls within JEDEC TO-220AB
- I. Tab contour optional within these dimensions



MECHANICAL INFORMATION

KTE (R-PSFM-T3)

PLASTIC FLANGE-MOUNT PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. The center lead is in electrical contact with the thermal tab.

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